Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A method of growing a metal silicate film on a substrate by atomic layer deposition comprising:

(i) introducing a metal organic precursor comprised of the formula:

$$M(NR^1 R^2)_n$$

and a silicon organic precursor comprised of a silicon alkyl amide of the formula:

$$Si(NR^1 R^2)_4$$

into a reaction chamber containing a substrate;

(ii) purging the reaction chamber;

(iii) introducing ozone into the reaction chamber;

(iv) purging the reaction chamber; and

(v) repeating steps (i), (ii), (iii) and (iv) until a film of a target thickness is achieved on the substrate,

wherein the temperature of the wafer is maintained between from about 100°C to about 500°C.

2. (Original) The method of claim 1, wherein the substrate is silicon.

3. (Currently amended) The method of claim 1, wherein M ~~the metal in the metal organic precursor~~ is a Group 4 metal.

4. (Currently amended) The method of claim 1, wherein M ~~the metal in the metal organic precursor~~ is hafnium.

5. (Original) The method of claim 1, wherein the metal organic precursor is a linear, branched and cyclic alkyl.

6. (Original) The method of claim 1, wherein the metal organic precursor is a metal alkyl amide.

7. (Canceled).

8. (Original) The method of claim 1, wherein the metal organic precursor is a metal alkoxide.

9. (Original) The method of claim 1, wherein the metal organic precursor and the silicon organic precursor are mixed, volatilized, and introduced into the chamber as a mixed gas.

10. (Original) The method of claim 1, wherein the metal organic precursor and the silicon organic precursor are volatilized separately and introduced into the chamber concurrently.

11. (Original) The method of claim 1, wherein the metal organic precursor and the silicon organic precursor are volatilized separately and introduced into the chamber consecutively.

12. (Currently Amended) A method of forming a gate for a transistor comprising:

(i) introducing a metal organic precursor comprised of the formula:

$$M(NR^1R^2)_n$$

and a silicon organic precursor comprised of a silicon alkyl amide of the formula:

$$Si(NR^1R^2)_4$$

into a reaction chamber containing a substrate;

(ii) purging the reaction chamber;

(iii) introducing ozone into the reaction chamber;

(iv) purging the reaction chamber;

(v) repeating steps (i), (ii), (iii) and (iv) until a dielectric film of a target thickness is achieved on the substrate; and

(vi) placing a conductive film over the dielectric film.

wherein the temperature of the wafer is maintained between from about 100°C to about 500°C.

13. (Original) The method of claim 12, wherein the substrate is silicon.

14. (Original) The method of claim 12, wherein the metal organic precursor is a linear, branched, and cyclic amide of Group 4 metal and wherein the silicon organic precursor is a silicon donating organic material.

15. (Original) The method of claim 12, wherein the metal organic precursor is a metal alkyl amide of a Group 4 metal, and wherein the silicon organic precursor is a silicon alkyl amide.

16. (Original) The method of claim 12, wherein the metal organic precursor and the silicon organic precursor are mixed, volatilized, and introduced into the chamber as a mixed gas.

17. (Original) The method of claim 12, wherein the metal organic precursor and the silicon organic precursor are volatilized separately and introduced into the chamber concurrently.

18. (Original) The method of claim 12, wherein the metal organic precursor and the silicon organic precursor are volatilized separately and introduced into the chamber consecutively.

19. (Currently Amended) A method of forming a capacitor comprising:

(i) introducing a metal organic precursor comprised of the formula:

$$M(NR^1R^2)_n$$

and a silicon organic precursor comprised of a silicon alkyl amide of the formula:

$$Si(NR^1R^2)_4$$

into a reaction chamber containing a substrate;

(ii) purging the reaction chamber;

(iii) introducing ozone into the reaction chamber;

(iv) purging the reaction chamber;

(v) repeating steps (i), (ii), (iii) and (iv) until a dielectric film of a target thickness is achieved on the substrate; and

(vi) positioning the film between two electrodes,

wherein the temperature of the wafer is maintained between from about 100°C to about 500°C.

20. (Original) The method of claim 19, wherein the substrate is one of the two electrodes.

21. (Original) The method of claim 19, wherein the metal organic precursor is a linear, branched and cyclic amide of Group 4 metal and wherein the silicon organic precursor is a silicon donating organic material.

22. (Original) The method of claim 19, wherein the metal organic precursor is a metal alkyl amide of a Group 4 metal, and wherein the silicon organic precursor is a silicon alkyl amide.

23. (Original) The method of claim 19, wherein the metal organic precursor and the silicon organic precursor are mixed, volatilized, and introduced into the chamber as a mixed gas.

24. (Original) The method of claim 19, wherein the metal organic precursor and the silicon organic precursor are volatilized separately and introduced into the chamber concurrently.

25. (Original) The method of claim 19, wherein the metal organic precursor and the silicon organic precursor are volatilized separately and introduced into the chamber consecutively.

26. (New) The method according to claim 1, wherein the temperature of the wafer is maintained between from about 200°C to about 400°C.

27. (New) The method according to claim 12, wherein the temperature of the wafer is maintained between from about 200°C to about 400°C.

28. (New) The method according to claim 19, wherein the temperature of the wafer is maintained between from about 200°C to about 400°C.